



Product Overview

NTMD4840N: Power MOSFET 30V 7.5A 24 mOhm Dual N-Channel SO-8

For complete documentation, see the data sheet

Product Description

Power MOSFET 30 V, 7 A, Dual N-Channel, SOIC-8

Features

- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- Dual SOIC-8 Surface Mount Package Saves Board Space
- This is a Pb-Free Device

Applications

- Disk Drives
- DC-DC Converters
- Printers

Part Electrical Specifications

| Product | Compliance | Status | Channel Polarity | Configuration | $V_{DS(sat)}$ Min (V) | V_{GS} Max (V) | $V_{GS(th)}$ Max (V) | I_D Max (A) | P_D Max (W) | $r_{DS(on)}$ Max @ $V_{GS} = 2.5$ V (m) | $r_{DS(on)}$ Max @ $V_{GS} = 4.5$ V (m) | $r_{DS(on)}$ Max @ $V_{GS} = 10$ V (m) | Q_g Typ @ $V_{GS} = 4.5$ V (nC) | Q_g Typ @ $V_{GS} = 10$ V (nC) | Q_{gd} Typ @ $V_{GS} = 4.5$ V (nC) | Q_{rr} Typ (nC) | C_{iss} Typ (pF) | C_{oss} Typ (pF) | C_{rss} Typ (pF) | Package Type |
|--------------|------------------------|--------|------------------|---------------|-----------------------|------------------|----------------------|---------------|---------------|---|---|--|-----------------------------------|----------------------------------|--------------------------------------|-------------------|--------------------|--------------------|--------------------|--------------|
| NTMD4840NR2G | Pb-free Halide free | Active | N-Channel | Dual | 30 | 20 | 3 | 7.5 | 1.95 | | 36 | 24 | 4.8 | | 1.9 | 6 | 520 | 140 | 70 | SOIC-8 |

For more information please contact your local sales support at www.onsemi.com

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